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ABSTRACT

In order to fabricate a high performance thin film semiconductor device using a low temperature process in which it is possible to use low price glass substrates, a thin film semiconductor device has been fabricated by forming a silicon film at less than 450°C, and, after crystallization, keeping the maximum processing temperature at or below 350°C.

In applying the present invention to the fabrication of an active matrix liquid crystal display, it is possible to both easily and reliably fabricate a large, high-quality liquid crystal display. Additionally, in applying the present invention to the fabrication of other electronic circuits as well, it is possible to both easily and reliably fabricate high-quality electronic circuits.

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